

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	45	isotropic and anisotropic same etch\$3 with diamond	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/07 09:27
S1	20	US-0593335-\$ DID. OR US-5107315-\$ DID. OR US-20010000111-\$ DID. OR US-5455432-\$ DID. OR US-5350944-\$ DID. OR US-6025233-\$ DID. OR US-5523588-\$ DID. OR US-6025211-\$ DID. OR US-6657223-\$ DID. OR US-5114871-\$ DID. OR EP-0343962-\$ DID.	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 10:09
S2	530	(257/E21.618).COLS.	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/03 10:36
S3	401	S2 and @ad<"20050325"	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 10:38
S4	265	438/105.col.s.	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 10:46
S5	227	S4 and @ad<"20050325"	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 10:47
S6	222330	diamond	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 11:38

S7	4727	S6 and ((FET) or (field adj effect adj transistor) or (field-effect and transistor))	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 11:39
S8	2207	S7 and carbon	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 11:40
S9	1653	S8 and @ad<"20050325"	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 11:40
S10	318	S9 and carbon adj (layer or film)	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 12:18
S11	4	("2006/0151844").URPN.	USPAT	OR	ON	2008/04/03 14:48
S12	2	("4863529"   "4929986").PN.	US_PGPUB; USPAT; USOOR	OR	ON	2008/04/03 15:06
S13	27	("5107315").URPN.	USPAT	OR	ON	2008/04/03 15:06
S14	1	S13 and isotropic	USPAT	OR	ON	2008/04/03 15:55
S15	0	(isotropic\$4 adj etch) near ((diamond or carbon) adj (layer or film))	USPAT	OR	ON	2008/04/03 16:08
S16	0	(isotropic\$4 adj etch) with ((diamond or carbon) adj (layer or film))	USPAT	OR	ON	2008/04/03 16:08
S17	4	(isotropic\$4 adj etch) same ((diamond or carbon) adj (layer or film))	USPAT	OR	ON	2008/04/03 16:08
S18	0	S13 and anisotropic	USPAT	OR	ON	2008/04/03 16:25
S19	0	(anisotropic\$4 adj etch) near ((diamond or carbon) adj (layer or film))	USPAT	OR	ON	2008/04/03 16:25
S20	5	(anisotropic\$4 adj etch) with ((diamond or carbon) adj (layer or film))	USPAT	OR	ON	2008/04/03 16:25
S21	0	"20070203424".did.	USPAT	OR	ON	2008/04/03 16:49

S22	0	"20070203424".pn.	USPAT	OR	ON	2008/04/03 16:49
S23	0	"20070203424".pn.	USPAT	OR	ON	2008/04/03 16:49
S24	2	"20070203424".pn.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 16:51
S25	2107	FET near CMOS	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 18:14
S26	1016	FET near (pmos and nmos)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/03 18:23

4/7/2008 10:32:26 AM

C:\Documents and Settings\rquinn\My Documents\EAST\Workspaces\10593335 Method of making a field effect transistor with diamond-like carbon channel and resulting transistor.wsp